

PTO/SB/08A/B (09-06)

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Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)				Complete if Known	
				Application Number	10/774,890
				Filing Date	February 9, 2004
				First Named Inventor	Fitzgerald
				Art Unit	2818
				Examiner Name	D. A. Le
				Attorney Docket Number	ASC-049C1
Sheet	1	of	1		

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
DL	A353	US-6,881,630	04-19-2005	Song et al.	

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
DL	C338	Office action in Ex Parte Reexamination of U.S. Patent No. 6,703,688, March 12, 2007.	

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²Applicant is to place a check mark here if English language Translation is attached.

Examiner Signature	DL	Date Considered	5/2007
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		Number-Kind Code ² (if known)			
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A291	US-6,861,318-A1	03-01-2005	Murthy et al.	
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A300	US-6,974,733-A1	12-13-2005	Boyanov et al.	
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A307	US-20010009303-A1	07-26-2001	Tang et al.	
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A309	US-20020001948-A1	01-03-2002	Lee	
A310	US-20020019127-A1	02-14-2002	Givens	
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A312	US-20020052084-A1	05-02-2002	Fitzgerald	
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A338	US-20050112048-A1	05-26-2005	Tsakalakos et al.	
A339	US-20050130454-A1	06-16-2005	Murthy et al.	

Examiner Signature	<i>De</i>	Date Considered	5/2007
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<input checked="" type="checkbox"/>	A340	US-20050156169-A1	07-21-2005	Chu	
<input checked="" type="checkbox"/>	A341	US-20050156180-A1	07-21-2005	Zhang et al.	
<input type="checkbox"/>	A342	US-20050156210-A1	07-21-2005	Currie et al.	
<input type="checkbox"/>	A343	US-20050161711-A1	07-28-2005	Chu	
<input type="checkbox"/>	A344	US-20050167652-A1	08-04-2005	Hoffmann et al.	
<input type="checkbox"/>	A345	US-20050176204-A1	08-11-2005	Langdo et al.	
<input type="checkbox"/>	A346	US-20050250298-A1	11-10-2005	Bauer	
<input type="checkbox"/>	A347	US-20050277272-A1	12-15-2005	Singh et al.	
<input type="checkbox"/>	A348	US-20050280026-A1	12-22-2005	Isaacson et al.	
<input type="checkbox"/>	A349	US-20050280098-A1	12-22-2005	Shin et al.	
<input checked="" type="checkbox"/>	A350	US-20060008958-A1	01-12-2006	Yeo et al.	
<input checked="" type="checkbox"/>	A351	US-20060009001-A1	01-12-2006	Huang et al.	
<input type="checkbox"/>	A352	US-20060057825-A1	03-16-2006	Bude et al.	

FOREIGN PATENT DOCUMENTS						
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		Country Code ² -Number ³ -Kind Code ⁴ (if known)	MM-DD-YYYY			
<i>DL</i>	B49	EP-0390661	10-03-1990			
<i> </i>	B50	JP-4-74415	03-09-1992			
<i>DL</i>	B51	JP-2000-031491	01-28-2000			✓
	B52	JP-2002-324765	11-08-2002		abstract only	✓

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<input checked="" type="checkbox"/>	C174	Ahlgren et al., "A SiGe HBT BICMOS Technology for Mixed-Signal RF Applications," 1997 IEEE Bipolar/BiCMOS Circuits and Tech. Meeting 195.		
<input type="checkbox"/>	C175	Ahn et al., "Film Stress-Related Vacancy Supersaturation in Silicon Under Low-Pressure Chemical Vapor Deposited Silicon Nitride Films," 64 J. App. Physics 4914 (1988).		
<input type="checkbox"/>	C176	Aldrich et al., "Stability of C54 Titanium Germanosilicide on a Silicon-Germanium Alloy Substrate," 77 J. App. Physics 10, pp. 5107-5114 (1995).		
<input type="checkbox"/>	C177	AmberWave Systems Corporation's Second Supplemental Responses to Intel's Third Set of Interrogatories, U.S.D.C., District of Delaware, C.A. No. 05-301-KAJ (July 12, 2006).		
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<input type="checkbox"/>	C179	Antoniadis et al., "SOI Devices and Technology," Neuilly sur Seine, France, pp. 81-87 (1999).		
<input type="checkbox"/>	C180	Aoyama et al., "Facet formation mechanism of silicon selective epitaxial layer by Si ultrahigh vacuum chemical vapor deposition," 136 Journal of Crystal Growth, pp. 349-354 (1994).		
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	C195	Cowern et al., "Diffusion in Strained Si(Ge)," 72 Physical Review Letters 2585 (1994).	
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